

L Number	Hits	Search Text	DB	Time stamp
1	5150	(117/59) or (257/59) or (257/66) or (257/67) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25).CCLS.	USPAT; US-1GPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-1GPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002-08/29 10:00 2002-08/29 07:37
8	3	("*.*101").PN.	USPAT	
15	2	(",*101" "5246070").PN.	USPAT	2002-08/19 07:47
16	0	("513/53" "544617").PN.) and organic with EL electroluminescence electroluminescent	USPAT	2002-08/19 07:46
17	0	("513/43" "544617").PN.) and organic same EL electroluminescence electroluminescent	USPAT	2002-08/19 07:46
18	3	semiconductor-energy-laboratory.as.	USPAT	2002-08/19 07:48
19	4	semiconductor-energy-laboratory.as.	USPAT;	2002-08/19 07:51
26	7	sem.y.s. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor).	USPAT; US-1GPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-1GPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002-08/19 07:55
33	3	sem.y.s. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor and organic with (EL electroluminescent electroluminescence))	USPAT; US-1GPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002-08/19 08:00
40	0	sem.y.s. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor and organic with (EL electroluminescent electroluminescence)) and inert	USPAT;	2002-08/19 08:00
47	2	(117/67, or (157/59, or (257/65) or (257/66), or (257/71, or (257/347) or (257/350), or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with EL and gate with (field adj effect adj transistor FET) and single adj crystal sem.y.s. and single adj crystal	USPAT; US-1GPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002-08/19 08:38
54	2	(117/67) or (157/59) or (257/66) or (257/66), or (257/71) or (257/347) or (257/350), or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with EL electroluminescence (electroluminescent) and gate with (field sem.y.s. and single adj crystal sem.y.s. and single adj crystal	USPAT; US-1GPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002-08/29 08:43
61	8	(117/67, or (257/59) or (257/66) or (257/66), or (257/71) or (257/347) or (257/350), or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with EL electroluminescence (electroluminescent) and gate with (field sem.y.s. and single adj crystal sem.y.s. and single adj crystal	USPAT; US-1GPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002-08/29 08:44
68	8	(117/67, or (257/59) or (257/66) or (257/66), or (257/71) or (257/347) or (257/350), or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with EL electroluminescence (electroluminescent) and gate with (field sem.y.s. and single adj crystal sem.y.s. and single adj crystal	USPAT; US-1GPUB; EPO; JPO; DERWENT; IBM TDB	2002-08/29 08:44

75	5	((257/57) or (257/54) or (257/76, or (257/77) or (257/78) or (257/79) or (257/80) or (31/12) or (44/15)).CCLS., and inert adj matrix and organic with (EL adj) electroluminescence (EL adj) and gate with (field effect transistor FET bottom adj gate adj gate and single adj crystal and inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:17
82	80	((257/57) or (257/54) or (257/76, or (257/77) or (257/78) or (257/79) or (257/80) or (31/12) or (44/15)).CCLS.) and inert adj FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:25
89	1	6274c5 .UPPN.	USPAT	2002/08/19 09:55
90	14	("511101" "511102" "541103-2" "511104" "561105" "561106" "564107" "571008" "571009" "573101" "573102" "581101" "581102" "581103").PN.	USPAT	2002/08/19 09:56
91	0	((257/57) "511101" "511102" "541103-2" "551104" "571105" "571106" "571107" "571108" "581101" "581102" "581103").PN., and active adj matrix and organic with (EL electroluminescence electroluminescent) and gate with field adj effect adj transistor FET bottom adj gate top adj gate, and single adj crystal and (inert adj gas).	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:59
98	0	((257/57) "511101" "511102" "541103-2" "551104" "571105" "571106" "571107" "571108" "581101" "581102" "581103").PN., and active adj matrix and organic with (EL electroluminescence electroluminescent) and gate and single adj crystal and (inert adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 09:59
105	492	((257/57) or (257/54) or (257/66) or (257/65) or (257/71) or (257/747) or (257/80) or (31/12) or (44/15)).CCLS.) and inert gas with organic adj EL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:02
112	9	((257/57) or (257/54) or (257/66) or (257/65) or (257/71) or (257/747) or (257/80) or (31/12) or (44/15)).CCLS.) and inert adj gas with organic adj EL	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:02
119	0	((257/57) or (257/54) or (257/66) or (257/65) or (257/71) or (257/747) or (257/80) or (31/12) or (44/15)).CCLS.) and inert adj gas with organic adj EL same existing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:03
126	0	((257/57) or (257/54) or (257/66) or (257/65) or (257/71) or (257/747) or (257/80) or (31/12) or (44/15)).CCLS.) and inert adj gas same organic adj EL same existing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:03
133	0	((257/57) or (257/54) or (257/66) or (257/65) or (257/71) or (257/747) or (257/80) or (31/12) or (44/15)).CCLS.) and active adj matrix and organic with EL electroluminescence (EL adj) and gate with (field effect transistor FET bottom adj gate adj gate and single adj crystal and rare id gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:20

- 6 (((257/57) or (257/58) or (257/66) or
 (257/67) or (257/72) or (257/34) or
 (257/50)) or (117/512) or (446/15).CCLS.)
 and active adj matrix and (organic with
 (EL_electroluminescent) and gate with (field
 el-stripluminescent) and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate) and single adj crystal
 and helium ne argon ar krypton kr xenon
 xe nitrogen ni)
- 3 (((257/57) or (257/58) or (257/66) or
 (257/67) or (257/72) or (257/34) or
 (257/50)) or (313/512) or (446/15).CCLS.)
 and active adj matrix and organic with
 (EL_electroluminescent)
 and gate with (field
 el-stripluminescent) and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate) and single adj crystal
 and helium ne argon ar krypton kr xenon
 xe nitrogen ni)
- 3 (((257/57) or (257/58) or (257/66) or
 (257/67) or (257/72) or (257/34) or
 (257/50) or (313/512) or (446/15).CCLS.)
 and active adj matrix and organic with
 (EL_electroluminescent) and gate with (field
 el-stripluminescent) and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate) and single adj crystal
 and helium ne argon ar krypton kr xenon
 xe nitrogen ni)
- 3 (((257/57) or (257/58) or (257/66) or
 (257/67) or (257/72) or (257/34) or
 (257/50) or (313/512) or (446/15).CCLS.)
 and active adj matrix and organic with
 (EL_electroluminescent) and gate with (field
 el-stripluminescent) and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate) and single adj crystal
 and helium ne argon ar krypton kr xenon
 xe nitrogen ni)
- 1 (((257/57) or (257/58) or (257/66) or
 (257/67) or (257/72) or (257/34) or
 (257/50) or (313/512) or (446/15).CCLS.)
 and active adj matrix and organic with
 (EL_electroluminescent)
 and gate with (field
 el-stripluminescent) and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate) and single adj crystal
 and helium ne argon ar krypton kr xenon
 xe nitrogen ni and barium adj oxide
 silica adj gel drying)
- 1 (((257/57) or (257/58) or (257/66) or
 (257/67) or (257/72) or (257/34) or
 (257/50) or (313/512) or (446/15).CCLS.)
 and active adj matrix and organic with
 (EL_electroluminescent)
 and gate with (field
 el-stripluminescent) and gate with (field
 adj effect adj transistor FET bottom adj
 gate tip adj gate) and single adj crystal
 and helium ne argon ar krypton kr xenon
 xe nitrogen ni and (helium ne argon ar
 krypton kr xenon xe nitrogen ni and
 carbon adj silica adj gel drying)

USPAT; 2002/08/29 10:21
 US_PGPUB;
 EPO; JPO;
 DERWENT;
 IBM_TDB

USPAT; 2002/08/29 10:24
 EPO; JPO;
 DERWENT;
 IBM_TDB

USPAT; 2002/08/29 11:12
 EPO; JPO;
 DERWENT;
 IBM_TDB

USPAT; 2002/08/29 10:26
 EPO; JPO;
 DERWENT;
 IBM_TDB

USPAT; 2002/08/29 10:27
 EPO; JPO;
 DERWENT;
 IBM_TDB

USPAT; 2002/08/29 10:28
 EPO; JPO;
 DERWENT;
 IBM_TDB

USPAT; 2002/08/29 10:28
 EPO; JPO;
 DERWENT;
 IBM_TDB

183

1 (((257/57; or (257/59) or (257/66) or (257/64) or (257/72) or (257/347) or (257/510) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL + electroluminescent)) and gate with (field effect); adj transistor FET bottom adj adj gate top adj gate and single adj crystal and helium ne argon kr krypton kr xenon xe nitrogen n-i) and helium ne argon ar krypton kr xenon xe nitrogen n inert adj gas inert adj gas and (rare adj oxide silica adj gel drying)

USPAT; 2002/08/29 10:29
EPO; JPO;
DERWENT;
IBM_TDB

189

1 (((257/57) or (257/59) or (257/66) or (257/64) or (257/72) or (257/347) or (257/510) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence) and gate with (field effect); adj transistor FET bottom adj adj effect adj transistor FET bottom adj gate top adj gate and single adj crystal and helium ne argon kr krypton kr xenon xe nitrogen n-i) and helium ne argon ar krypton kr xenon xe nitrogen n inert adj gas inert adj gas and (rare adj oxide silica adj gel drying)

USPAT; 2002/08/29 11:14
EPO; JPO;
DERWENT;
IBM_TDB

195

4 (((257/57) or (257/59) or (257/66) or (257/64) or (257/72) or (257/347) or (257/510) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence)

USPAT; 2002/08/29 11:20
EPO; JPO;
DERWENT;
IBM_TDB

201

1 (((257/57) or (257/59) or (257/66) or (257/64) or (257/72) or (257/347) or (257/510) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and rare adj gas and barium adj oxide silica adj gel drying)

USPAT; 2002/08/29 11:15
EPO; JPO;
DERWENT;
IBM_TDB

207

4 (((257/57) or (257/59) or (257/66) or (257/64) or (257/72) or (257/347) or (257/510) or (313/512) or (445/25)).CCLS.) and matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal

USPAT; 2002/08/29 11:21
EPO; JPO;
DERWENT;
IBM_TDB

- 229 -445/25).CCLS.
- 343 -313/512).CCLS.
- 0 -445/25.ap.

USPAT 2002/08/28 14:30
USPAT 2002/08/28 14:39
USPAT 2002/08/28 14:39
US-PGPUB;
EPO; JPO;
DERWENT;
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- 1 -445/25.ap.

2002/08/28 14:39

- 229 -445/25).CCLS.
- 722 -313/512) or -445/25 -.CCLS.

USPAT 2002/08/28 14:48
USPAT 2002/08/28 14:48
EPO; JPO;
DERWENT;
IBM_TDB

17 (((313/512) or (445/25)).CCLS.) and active adj matrix USPAT; 2002/08/28 14:55
 13 (((13/512) or (445/25)).CCLS.) and active adj matrix USPAT; 2002/08/28 14:56
 1 (((313/512) or (445/25)).CCLS.) and active adj matrix and single adj crystal USPAT; 2002/08/28 14:58
 3 5672.83.USPN. USPAT; 2002/08/28 14:57
 1 ((13/512) or (445/25)).CCLS.) and active adj matrix and (field adj effect adj transistor FET) USPAT; 2002/08/28 15:01
 0 (257/\$).ccls. USPAT; 2002/08/28 15:01
 134751 (257/\$).ccls. USPAT; 2002/08/28 15:02
 66945 (313/8).ccls. USPAT; 2002/08/28 15:04
 8 (313/8).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) USPAT; 2002/08/28 15:32
 5 ((313/8).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal USPAT; 2002/08/28 15:25
 0 ((313/8).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal USPAT; 2002/08/28 16:14
 4347 ...57/57) or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350)).CCLS. USPAT; 2002/08/29 08:36
 2 ((257/57) or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal USPAT; 2002/08/28 15:31
 4396 yamazaki-shunpei.in. or arai-yasuyuki.in. USPAT; 2002/08/28 15:31

4178 yamazaki-shunpei.in.

943 yamazaki-shunpei.in. or arai-yasuyuki.in.
1171 yamazaki-shunpei.in. or arai-yasuyuki.in.

- 0 (yamazaki-shunpei.in. or
arai-yasuyuki.in.) and active adj matrix
and (organic with EL) and gate with (field
adj effect adj transistor FET) and single
adj crystal
- 1 (yamazaki-shunpei.in. or
arai-yasuyuki.in.) and active adj matrix
and (organic with EL) and gate with (field
adj effect adj transistor FET) and single
adj crystal
- 3 1139545.USPN.
- 2 ((257/57) cr (257/59) or (257/66) or
(257/66) or (257/72) or (257/347) or
(257/350)).CCLS.) and active adj matrix
and (organic with EL) and gate with (field
adj effect adj transistor FET mostft) and
single adj crystal
- 5136 ((257/57) or (257/59) or (257/66) cr
(257/66) or (257/72) or (257/347) or
(257/350) or (313/512) or (445/25)).CCLS.
- 2 ((257/57) or (257/59) or (257/66) or
(257/66) or (257/72) or (257/347) or
(257/350) or (313/512) or (445/25)).CCLS.
and active adj matrix and (organic with
EL) and gate with (field adj effect adj
transistor FET mostft) and single adj
crystal
- 2 ("613893" | "6246070").PN.

USPAT; 2002/08/28 15:31
US-PGPUB;
EPO; JPO;
DEFWENT;
IBM_TDB
USPAT; 2002/08/28 15:32
USPAT; 2002/08/28 15:32
US-PGPUB
USPAT; 2002/08/28 15:33
US-PGPUB;
EPO; JPO;
DEFWENT;
IBM_TDB
USPAT; 2002/08/28 15:33
US-PGPUB;
EPO; JPO;
DEFWENT;
IBM_TDB
USPAT; 2002/08/28 15:35
USPAT; 2002/08/28 16:15
US-PGPUB;
EPO; JPO;
DEFWENT;
IBM_TDB
USPAT; 2002/08/29 07:37
US-PGPUB;
EPO; JPO;
DEFWENT;
IBM_TDB
USPAT; 2002/08/28 16:15
US-PGPUB;
EPO; JPO;
DEFWENT;
IBM_TDB
USPAT 2002/08/28 16:27